

Supporting Information

Unconventional Strain-Dependent Conductance Oscillations in Pristine Phosphorene

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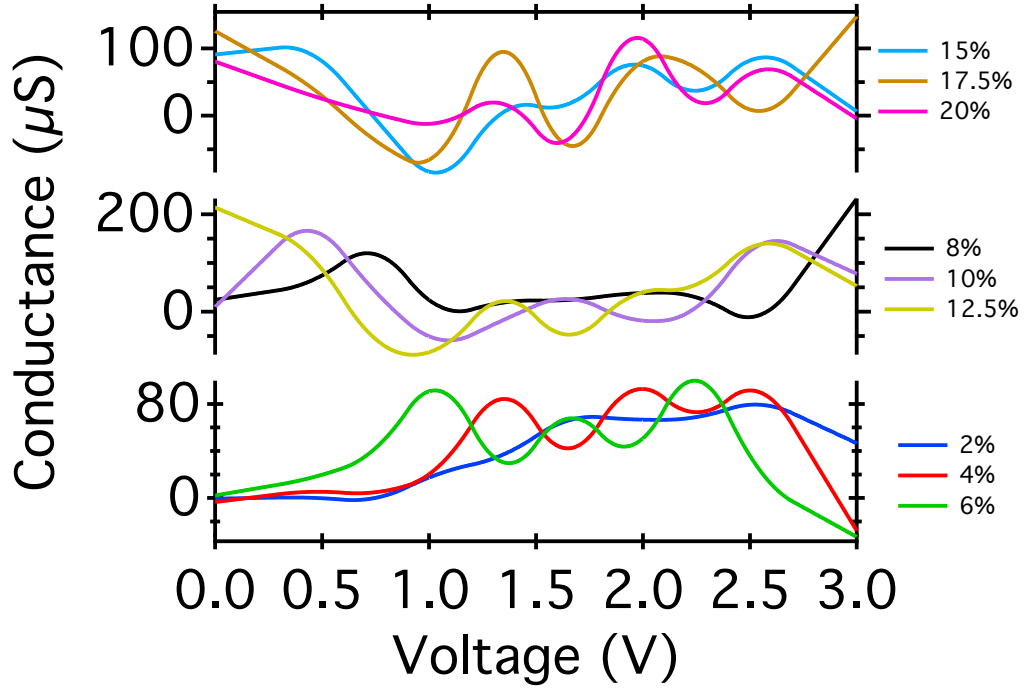


FIG. S1: Differential Conductance (dI/dV) as function of applied bias for various values of S_Z , corresponding to I_{AZ} geometry.

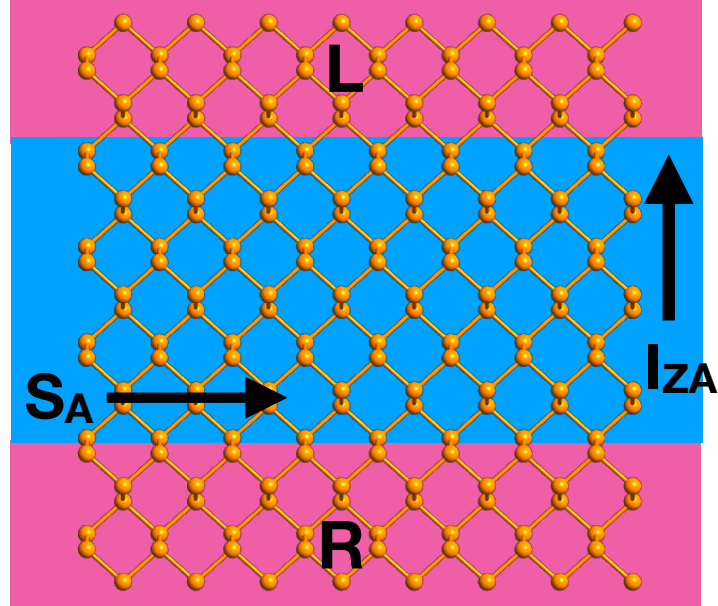


FIG. S2: Two-probe conduction geometry in Phosphorene for external strain applied along the armchair direction (S_A) and current measured along the zigzag direction (I_{ZA}).

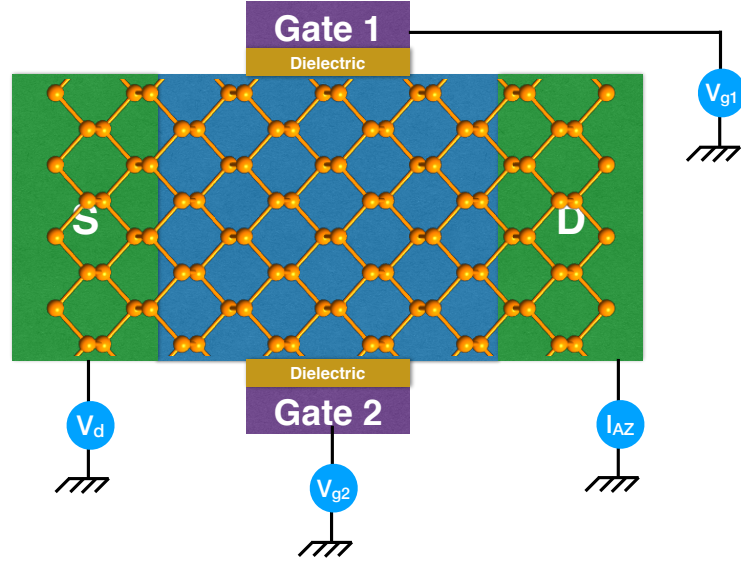


FIG. S3: Phosphorene based Field effect Transistor in lateral gate geometry. Two gate electrodes are placed on two sides of the channel area in the same plane.